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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	8375
Number of Logic Elements/Cells	67000
Total RAM Bits	4526080
Number of I/O	490
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	1156-BBGA
Supplier Device Package	1156-FPBGA (35x35)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe3-70ea-6lfn1156i

Features

■ Higher Logic Density for Increased System Integration

- 17K to 149K LUTs
- 116 to 586 I/Os

■ Embedded SERDES

- 150 Mbps to 3.2 Gbps for Generic 8b10b, 10-bit SERDES, and 8-bit SERDES modes
- Data Rates 230 Mbps to 3.2 Gbps per channel for all other protocols
- Up to 16 channels per device: PCI Express, SONET/SDH, Ethernet (1GbE, SGMII, XAUI), CPRI, SMPTE 3G and Serial RapidIO

■ sysDSP™

- Fully cascadable slice architecture
- 12 to 160 slices for high performance multiply and accumulate
- Powerful 54-bit ALU operations
- Time Division Multiplexing MAC Sharing
- Rounding and truncation
- Each slice supports
 - Half 36x36, two 18x18 or four 9x9 multipliers
 - Advanced 18x36 MAC and 18x18 Multiply-Multiply-Accumulate (MMAC) operations

■ Flexible Memory Resources

- Up to 6.85Mbits sysMEM™ Embedded Block RAM (EBR)
- 36K to 303K bits distributed RAM

■ sysCLOCK Analog PLLs and DLLs

- Two DLLs and up to ten PLLs per device

■ Pre-Engineered Source Synchronous I/O

- DDR registers in I/O cells

- Dedicated read/write levelling functionality
- Dedicated gearing logic
- Source synchronous standards support
 - ADC/DAC, 7:1 LVDS, XGMII
 - High Speed ADC/DAC devices
- Dedicated DDR/DDR2/DDR3 memory with DQS support
- Optional Inter-Symbol Interference (ISI) correction on outputs

■ Programmable sysI/O™ Buffer Supports Wide Range of Interfaces

- On-chip termination
- Optional equalization filter on inputs
- LVTTL and LVCMOS 33/25/18/15/12
- SSTL 33/25/18/15 I, II
- HSTL15 I and HSTL18 I, II
- PCI and Differential HSTL, SSTL
- LVDS, Bus-LVDS, LVPECL, RSDS, MLVDS

■ Flexible Device Configuration

- Dedicated bank for configuration I/Os
- SPI boot flash interface
- Dual-boot images supported
- Slave SPI
- TransFR™ I/O for simple field updates
- Soft Error Detect embedded macro

■ System Level Support

- IEEE 1149.1 and IEEE 1532 compliant
- Reveal Logic Analyzer
- ORCAstra FPGA configuration utility
- On-chip oscillator for initialization & general use
- 1.2 V core power supply

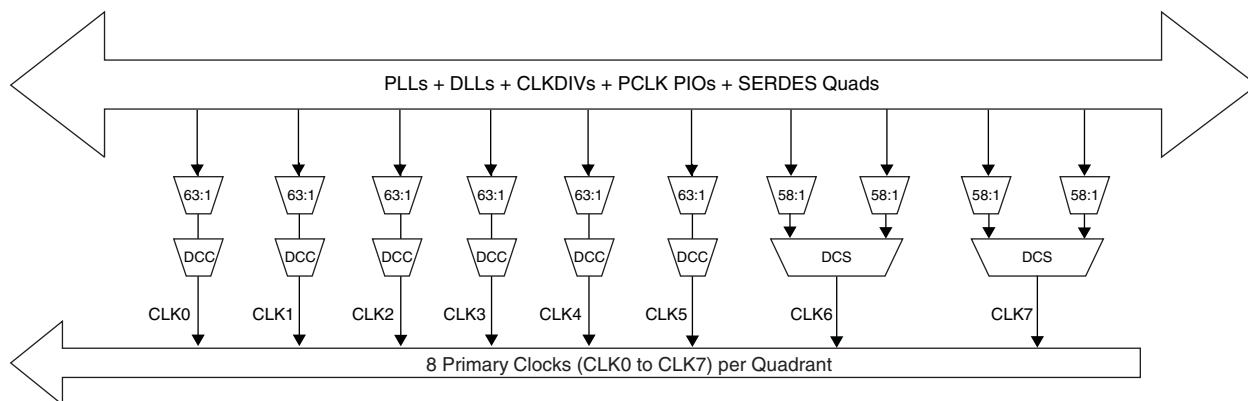
Table 1-1. LatticeECP3™ Family Selection Guide

Device	ECP3-17	ECP3-35	ECP3-70	ECP3-95	ECP3-150
LUTs (K)	17	33	67	92	149
sysMEM Blocks (18 Kbits)	38	72	240	240	372
Embedded Memory (Kbits)	700	1327	4420	4420	6850
Distributed RAM Bits (Kbits)	36	68	145	188	303
18 x 18 Multipliers	24	64	128	128	320
SERDES (Quad)	1	1	3	3	4
PLLs/DLLs	2 / 2	4 / 2	10 / 2	10 / 2	10 / 2
Packages and SERDES Channels/ I/O Combinations					
328 csBGA (10 x 10 mm)	2 / 116				
256 ftBGA (17 x 17 mm)	4 / 133	4 / 133			
484 fpBGA (23 x 23 mm)	4 / 222	4 / 295	4 / 295	4 / 295	
672 fpBGA (27 x 27 mm)		4 / 310	8 / 380	8 / 380	8 / 380
1156 fpBGA (35 x 35 mm)			12 / 490	12 / 490	16 / 586

Primary Clock Routing

The purpose of the primary clock routing is to distribute primary clock sources to the destination quadrants of the device. A global primary clock is a primary clock that is distributed to all quadrants. The clock routing structure in LatticeECP3 devices consists of a network of eight primary clock lines (CLK0 through CLK7) per quadrant. The primary clocks of each quadrant are generated from muxes located in the center of the device. All the clock sources are connected to these muxes. Figure 2-12 shows the clock routing for one quadrant. Each quadrant mux is identical. If desired, any clock can be routed globally.

Figure 2-12. Per Quadrant Primary Clock Selection



Dynamic Clock Control (DCC)

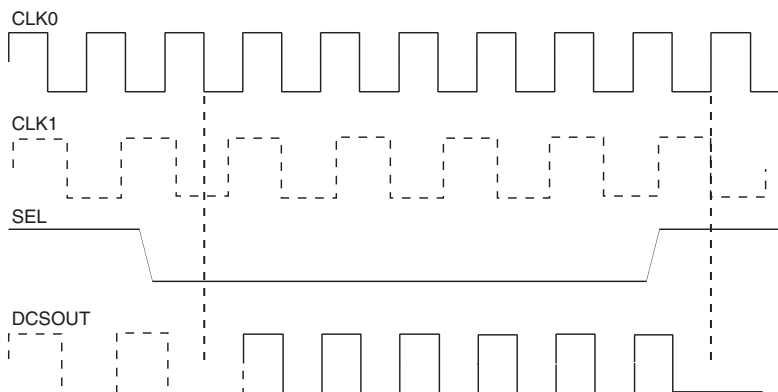
The DCC (Quadrant Clock Enable/Disable) feature allows internal logic control of the quadrant primary clock network. When a clock network is disabled, all the logic fed by that clock does not toggle, reducing the overall power consumption of the device.

Dynamic Clock Select (DCS)

The DCS is a smart multiplexer function available in the primary clock routing. It switches between two independent input clock sources without any glitches or runt pulses. This is achieved regardless of when the select signal is toggled. There are two DCS blocks per quadrant; in total, there are eight DCS blocks per device. The inputs to the DCS block come from the center muxes. The output of the DCS is connected to primary clocks CLK6 and CLK7 (see Figure 2-12).

Figure 2-13 shows the timing waveforms of the default DCS operating mode. The DCS block can be programmed to other modes. For more information about the DCS, please see the list of technical documentation at the end of this data sheet.

Figure 2-13. DCS Waveforms

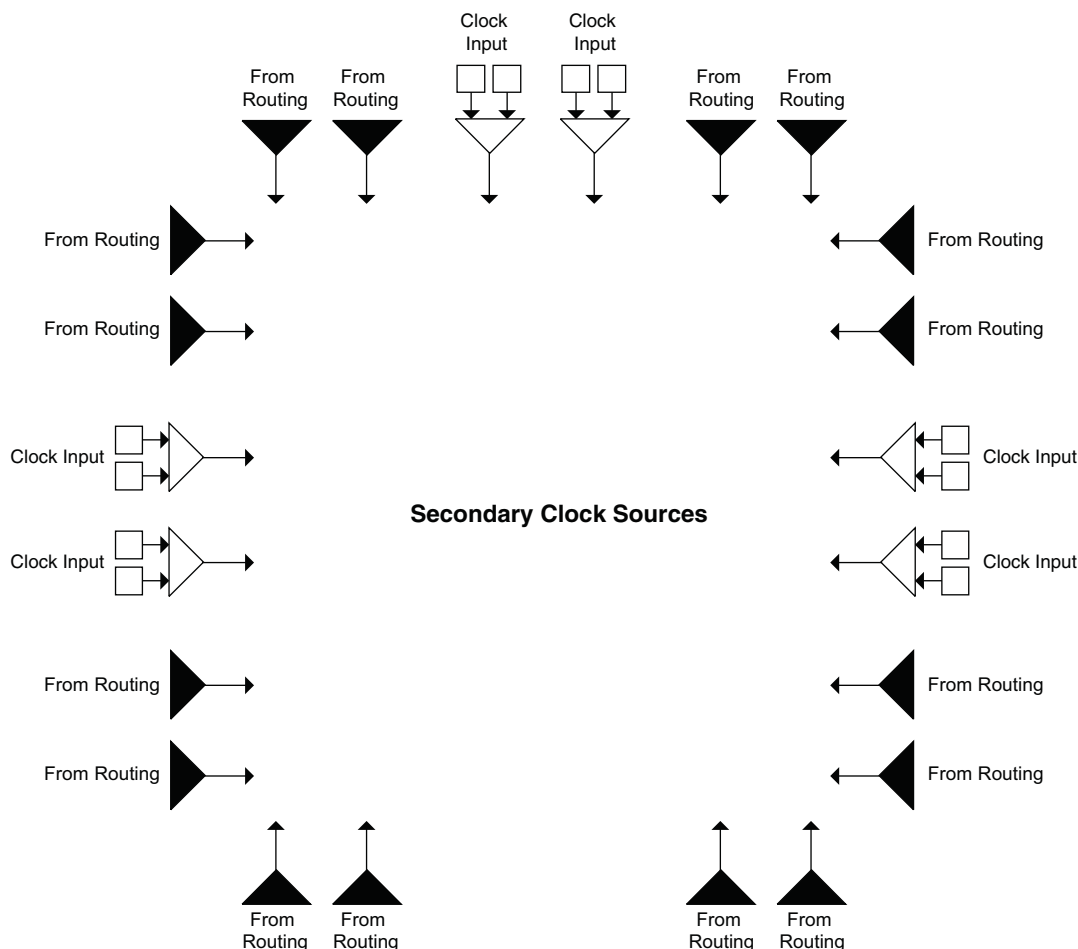


Secondary Clock/Control Sources

LatticeECP3 devices derive eight secondary clock sources (SC0 through SC7) from six dedicated clock input pads and the rest from routing. Figure 2-14 shows the secondary clock sources. All eight secondary clock sources are defined as inputs to a per-region mux SC0-SC7. SC0-SC3 are primary for control signals (CE and/or LSR), and SC4-SC7 are for the clock.

In an actual implementation, there is some overlap to maximize routability. In addition to SC0-SC3, SC7 is also an input to the control signals (LSR or CE). SC0-SC2 are also inputs to clocks along with SC4-SC7.

Figure 2-14. Secondary Clock Sources



Note: Clock inputs can be configured in differential or single-ended mode.

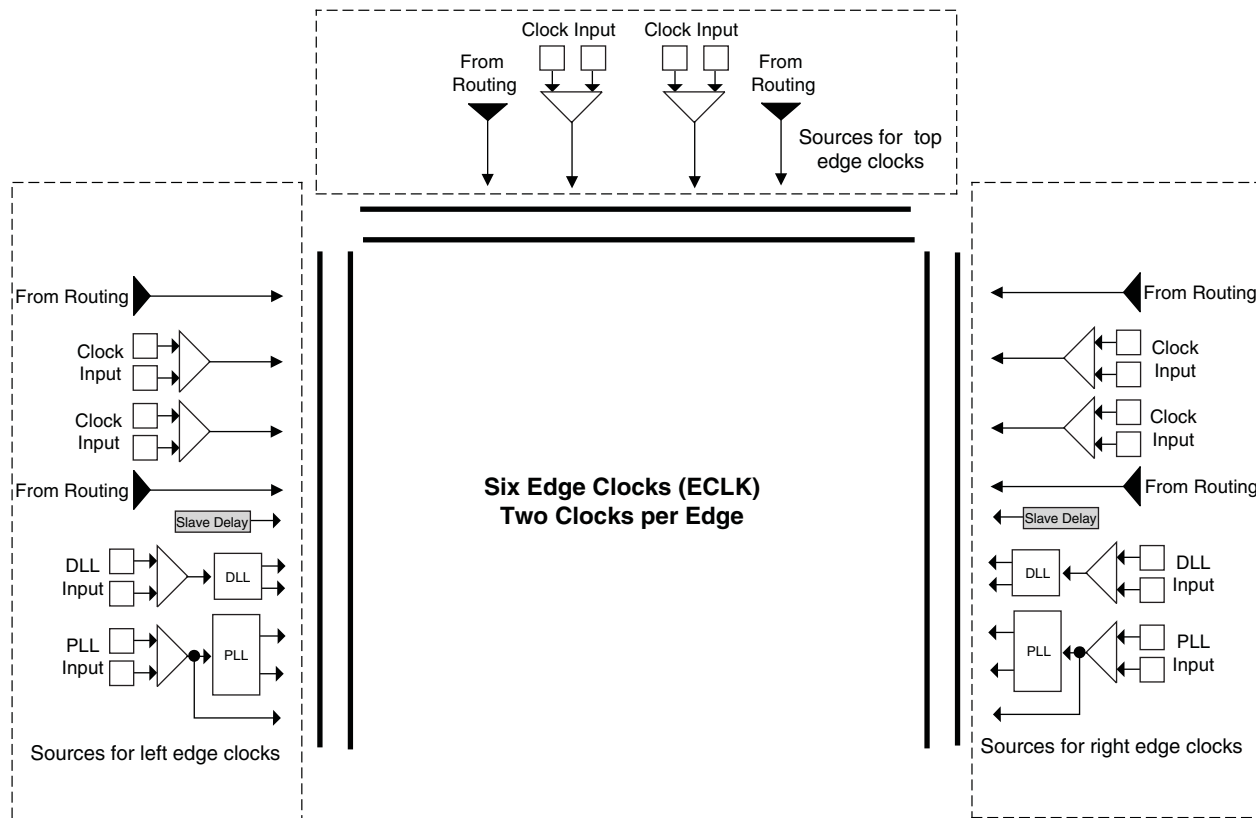
Secondary Clock/Control Routing

Global secondary clock is a secondary clock that is distributed to all regions. The purpose of the secondary clock routing is to distribute the secondary clock sources to the secondary clock regions. Secondary clocks in the LatticeECP3 devices are region-based resources. Certain EBR rows and special vertical routing channels bind the secondary clock regions. This special vertical routing channel aligns with either the left edge of the center DSP slice in the DSP row or the center of the DSP row. Figure 2-15 shows this special vertical routing channel and the 20 secondary clock regions for the LatticeECP3 family of devices. All devices in the LatticeECP3 family have eight secondary clock resources per region (SC0 to SC7). The same secondary clock routing can be used for control signals.

Edge Clock Sources

Edge clock resources can be driven from a variety of sources at the same edge. Edge clock resources can be driven from adjacent edge clock PIOs, primary clock PIOs, PLLs, DLLs, Slave Delay and clock dividers as shown in Figure 2-19.

Figure 2-19. Edge Clock Sources



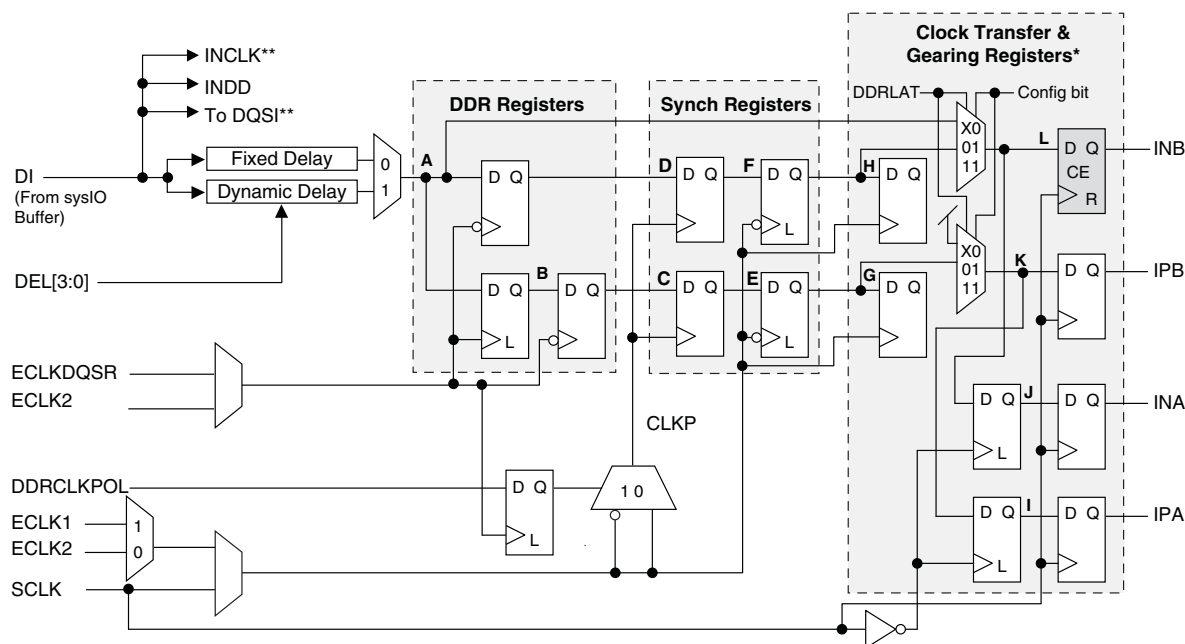
Notes:

1. Clock inputs can be configured in differential or single ended mode.
2. The two DLLs can also drive the two top edge clocks.
3. The top left and top right PLL can also drive the two top edge clocks.

Edge Clock Routing

LatticeECP3 devices have a number of high-speed edge clocks that are intended for use with the PIOs in the implementation of high-speed interfaces. There are six edge clocks per device: two edge clocks on each of the top, left, and right edges. Different PLL and DLL outputs are routed to the two muxes on the left and right sides of the device. In addition, the CLKINDEL signal (generated from the DLL Slave Delay Line block) is routed to all the edge clock muxes on the left and right sides of the device. Figure 2-20 shows the selection muxes for these clocks.

Figure 2-33. Input Register Block for Left, Right and Top Edges



* Only on the left and right sides.
** Selected PIO.
Note: Simplified diagram does not show CE/SET/REST details.

Output Register Block

The output register block registers signals from the core of the device before they are passed to the sysIO buffers. The blocks on the left and right PIOs contain registers for SDR and full DDR operation. The topside PIO block is the same as the left and right sides except it does not support ODDR2 gearing of output logic. ODDR2 gearing is used in DDR3 memory interfaces. The PIO blocks on the bottom contain the SDR registers but do not support generic DDR.

Figure 2-34 shows the Output Register Block for PIOs on the left and right edges.

In SDR mode, OPOSA feeds one of the flip-flops that then feeds the output. The flip-flop can be configured as a Dtype or latch. In DDR mode, two of the inputs are fed into registers on the positive edge of the clock. At the next clock cycle, one of the registered outputs is also latched.

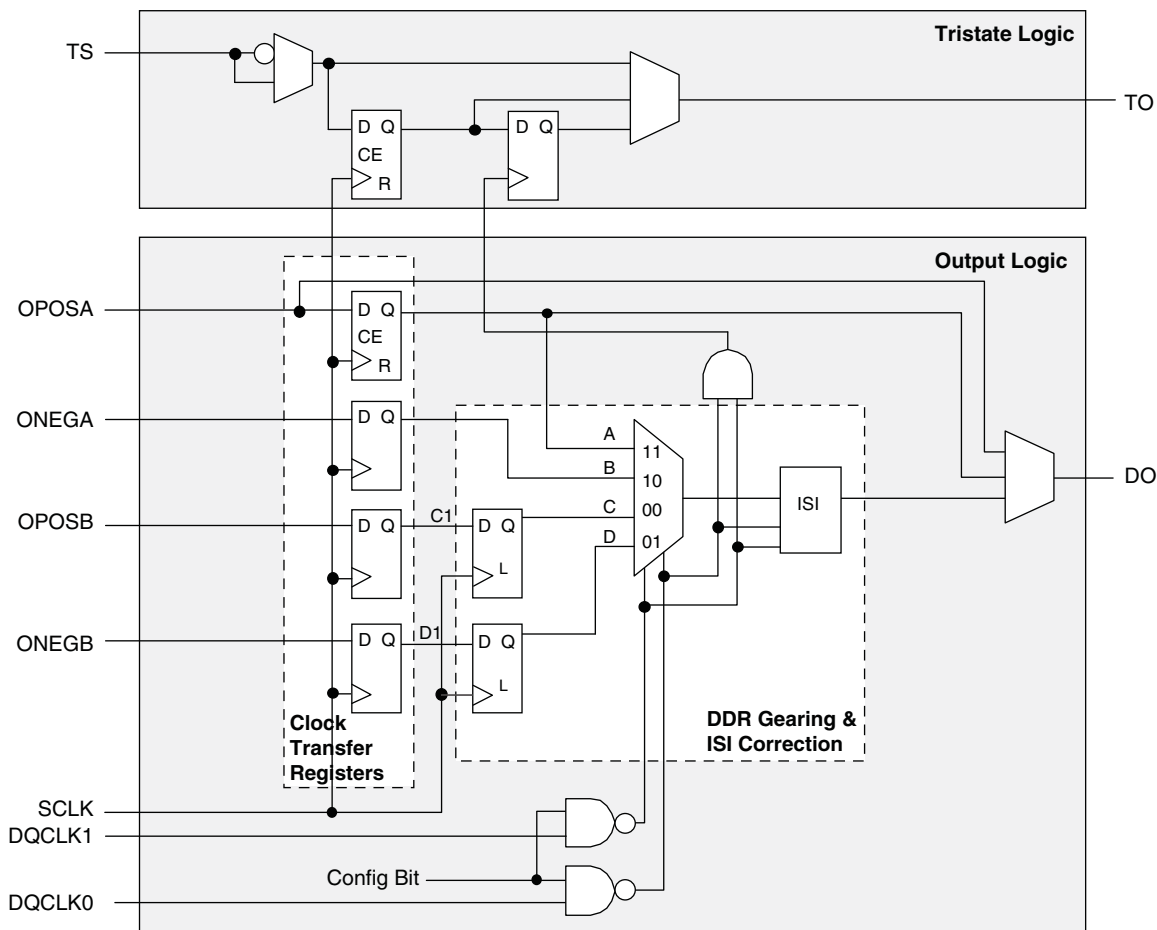
A multiplexer running off the same clock is used to switch the mux between the 11 and 01 inputs that will then feed the output.

A gearbox function can be implemented in the output register block that takes four data streams: OPOSA, ONEGA, OPOSB and ONEGB. All four data inputs are registered on the positive edge of the system clock and two of them are also latched. The data is then output at a high rate using a multiplexer that runs off the DQCLK0 and DQCLK1 clocks. DQCLK0 and DQCLK1 are used in this case to transfer data from the system clock to the edge clock domain. These signals are generated in the DQS Write Control Logic block. See Figure 2-37 for an overview of the DQS write control logic.

Please see TN1180, [LatticeECP3 High-Speed I/O Interface](#) for more information on this topic.

Further discussion on using the DQS strobe in this module is discussed in the DDR Memory section of this data sheet.

Figure 2-34. Output and Tristate Block for Left and Right Edges



Tristate Register Block

The tristate register block registers tri-state control signals from the core of the device before they are passed to the sysI/O buffers. The block contains a register for SDR operation and an additional register for DDR operation.

In SDR and non-gearing DDR modes, TS input feeds one of the flip-flops that then feeds the output. In DDRX2 mode, the register TS input is fed into another register that is clocked using the DQCLK0 and DQCLK1 signals. The output of this register is used as a tristate control.

ISI Calibration

The setting for Inter-Symbol Interference (ISI) cancellation occurs in the output register block. ISI correction is only available in the DDRX2 modes. ISI calibration settings exist once per output register block, so each I/O in a DQS-12 group may have a different ISI calibration setting.

The ISI block extends output signals at certain times, as a function of recent signal history. So, if the output pattern consists of a long strings of 0's to long strings of 1's, there are no delays on output signals. However, if there are quick, successive transitions from 010, the block will stretch out the binary 1. This is because the long trail of 0's will cause these symbols to interfere with the logic 1. Likewise, if there are quick, successive transitions from 101, the block will stretch out the binary 0. This block is controlled by a 3-bit delay control that can be set in the DQS control logic block.

For more information about this topic, please see the list of technical documentation at the end of this data sheet.

DC Electrical Characteristics

Over Recommended Operating Conditions

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
$I_{IL}, I_{IH}^{1,4}$	Input or I/O Low Leakage	$0 \leq V_{IN} \leq (V_{CCIO} - 0.2 \text{ V})$	—	—	10	μA
$I_{IH}^{1,3}$	Input or I/O High Leakage	$(V_{CCIO} - 0.2 \text{ V}) < V_{IN} \leq 3.6 \text{ V}$	—	—	150	μA
I_{PU}	I/O Active Pull-up Current	$0 \leq V_{IN} \leq 0.7 V_{CCIO}$	-30	—	-210	μA
I_{PD}	I/O Active Pull-down Current	$V_{IL} (\text{MAX}) \leq V_{IN} \leq V_{CCIO}$	30	—	210	μA
I_{BHLS}	Bus Hold Low Sustaining Current	$V_{IN} = V_{IL} (\text{MAX})$	30	—	—	μA
I_{BHHS}	Bus Hold High Sustaining Current	$V_{IN} = 0.7 V_{CCIO}$	-30	—	—	μA
I_{BHLO}	Bus Hold Low Overdrive Current	$0 \leq V_{IN} \leq V_{CCIO}$	—	—	210	μA
I_{BHHO}	Bus Hold High Overdrive Current	$0 \leq V_{IN} \leq V_{CCIO}$	—	—	-210	μA
V_{BHT}	Bus Hold Trip Points	$0 \leq V_{IN} \leq V_{IH} (\text{MAX})$	$V_{IL} (\text{MAX})$	—	$V_{IH} (\text{MIN})$	V
C1	I/O Capacitance ²	$V_{CCIO} = 3.3 \text{ V}, 2.5 \text{ V}, 1.8 \text{ V}, 1.5 \text{ V}, 1.2 \text{ V},$ $V_{CC} = 1.2 \text{ V}, V_{IO} = 0 \text{ to } V_{IH} (\text{MAX})$	—	5	8	pf
C2	Dedicated Input Capacitance ²	$V_{CCIO} = 3.3 \text{ V}, 2.5 \text{ V}, 1.8 \text{ V}, 1.5 \text{ V}, 1.2 \text{ V},$ $V_{CC} = 1.2 \text{ V}, V_{IO} = 0 \text{ to } V_{IH} (\text{MAX})$	—	5	7	pf

1. Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tri-stated. It is not measured with the output driver active. Bus maintenance circuits are disabled.

2. $T_A = 25^\circ\text{C}$, $f = 1.0 \text{ MHz}$.

3. Applicable to general purpose I/Os in top and bottom banks.

4. When used as V_{REF} maximum leakage = $25 \mu\text{A}$.

LatticeECP3 External Switching Characteristics ^{1, 2, 3, 13}

Over Recommended Commercial Operating Conditions

Parameter	Description	Device	–8		–7		–6		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
Clocks									
Primary Clock ⁶									
f _{MAX_PRI}	Frequency for Primary Clock Tree	ECP3-150EA	—	500	—	420	—	375	MHz
t _{W_PRI}	Clock Pulse Width for Primary Clock	ECP3-150EA	0.8	—	0.9	—	1.0	—	ns
t _{SKEW_PRI}	Primary Clock Skew Within a Device	ECP3-150EA	—	300	—	330	—	360	ps
t _{SKEW_PRIIB}	Primary Clock Skew Within a Bank	ECP3-150EA	—	250	—	280	—	300	ps
f _{MAX_PRI}	Frequency for Primary Clock Tree	ECP3-70EA/95EA	—	500	—	420	—	375	MHz
t _{W_PRI}	Pulse Width for Primary Clock	ECP3-70EA/95EA	0.8	—	0.9	—	1.0	—	ns
t _{SKEW_PRI}	Primary Clock Skew Within a Device	ECP3-70EA/95EA	—	360	—	370	—	380	ps
t _{SKEW_PRIIB}	Primary Clock Skew Within a Bank	ECP3-70EA/95EA	—	310	—	320	—	330	ps
f _{MAX_PRI}	Frequency for Primary Clock Tree	ECP3-35EA	—	500	—	420	—	375	MHz
t _{W_PRI}	Pulse Width for Primary Clock	ECP3-35EA	0.8	—	0.9	—	1.0	—	ns
t _{SKEW_PRI}	Primary Clock Skew Within a Device	ECP3-35EA	—	300	—	330	—	360	ps
t _{SKEW_PRIIB}	Primary Clock Skew Within a Bank	ECP3-35EA	—	250	—	280	—	300	ps
f _{MAX_PRI}	Frequency for Primary Clock Tree	ECP3-17EA	—	500	—	420	—	375	MHz
t _{W_PRI}	Pulse Width for Primary Clock	ECP3-17EA	0.8	—	0.9	—	1.0	—	ns
t _{SKEW_PRI}	Primary Clock Skew Within a Device	ECP3-17EA	—	310	—	340	—	370	ps
t _{SKEW_PRIIB}	Primary Clock Skew Within a Bank	ECP3-17EA	—	220	—	230	—	240	ps
Edge Clock ⁶									
f _{MAX_EDGE}	Frequency for Edge Clock	ECP3-150EA	—	500	—	420	—	375	MHz
t _{W_EDGE}	Clock Pulse Width for Edge Clock	ECP3-150EA	0.9	—	1.0	—	1.2	—	ns
t _{SKEW_EDGE_DQS}	Edge Clock Skew Within an Edge of the Device	ECP3-150EA	—	200	—	210	—	220	ps
f _{MAX_EDGE}	Frequency for Edge Clock	ECP3-70EA/95EA	—	500	—	420	—	375	MHz
t _{W_EDGE}	Clock Pulse Width for Edge Clock	ECP3-70EA/95EA	0.9	—	1.0	—	1.2	—	ns
t _{SKEW_EDGE_DQS}	Edge Clock Skew Within an Edge of the Device	ECP3-70EA/95EA	—	200	—	210	—	220	ps
f _{MAX_EDGE}	Frequency for Edge Clock	ECP3-35EA	—	500	—	420	—	375	MHz
t _{W_EDGE}	Clock Pulse Width for Edge Clock	ECP3-35EA	0.9	—	1.0	—	1.2	—	ns
t _{SKEW_EDGE_DQS}	Edge Clock Skew Within an Edge of the Device	ECP3-35EA	—	200	—	210	—	220	ps
f _{MAX_EDGE}	Frequency for Edge Clock	ECP3-17EA	—	500	—	420	—	375	MHz
t _{W_EDGE}	Clock Pulse Width for Edge Clock	ECP3-17EA	0.9	—	1.0	—	1.2	—	ns
t _{SKEW_EDGE_DQS}	Edge Clock Skew Within an Edge of the Device	ECP3-17EA	—	200	—	210	—	220	ps
Generic SDR									
General I/O Pin Parameters Using Dedicated Clock Input Primary Clock Without PLL ²									
t _{CO}	Clock to Output - PIO Output Register	ECP3-150EA	—	3.9	—	4.3	—	4.7	ns
t _{SU}	Clock to Data Setup - PIO Input Register	ECP3-150EA	0.0	—	0.0	—	0.0	—	ns
t _H	Clock to Data Hold - PIO Input Register	ECP3-150EA	1.5	—	1.7	—	2.0	—	ns
t _{SU_DEL}	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-150EA	1.3	—	1.5	—	1.7	—	ns

Figure 3-6. Generic DDRX1/DDR2 (With Clock and Data Edges Aligned)

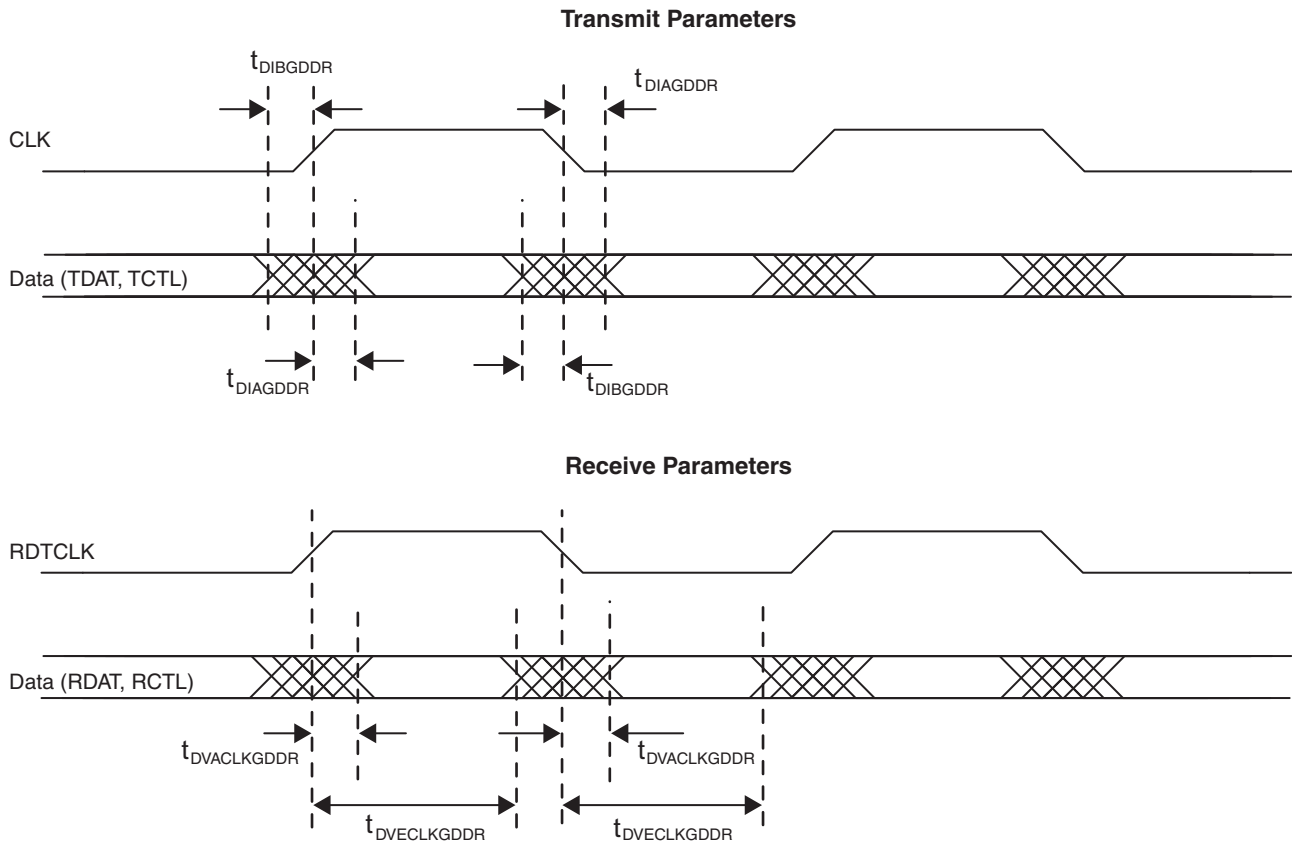
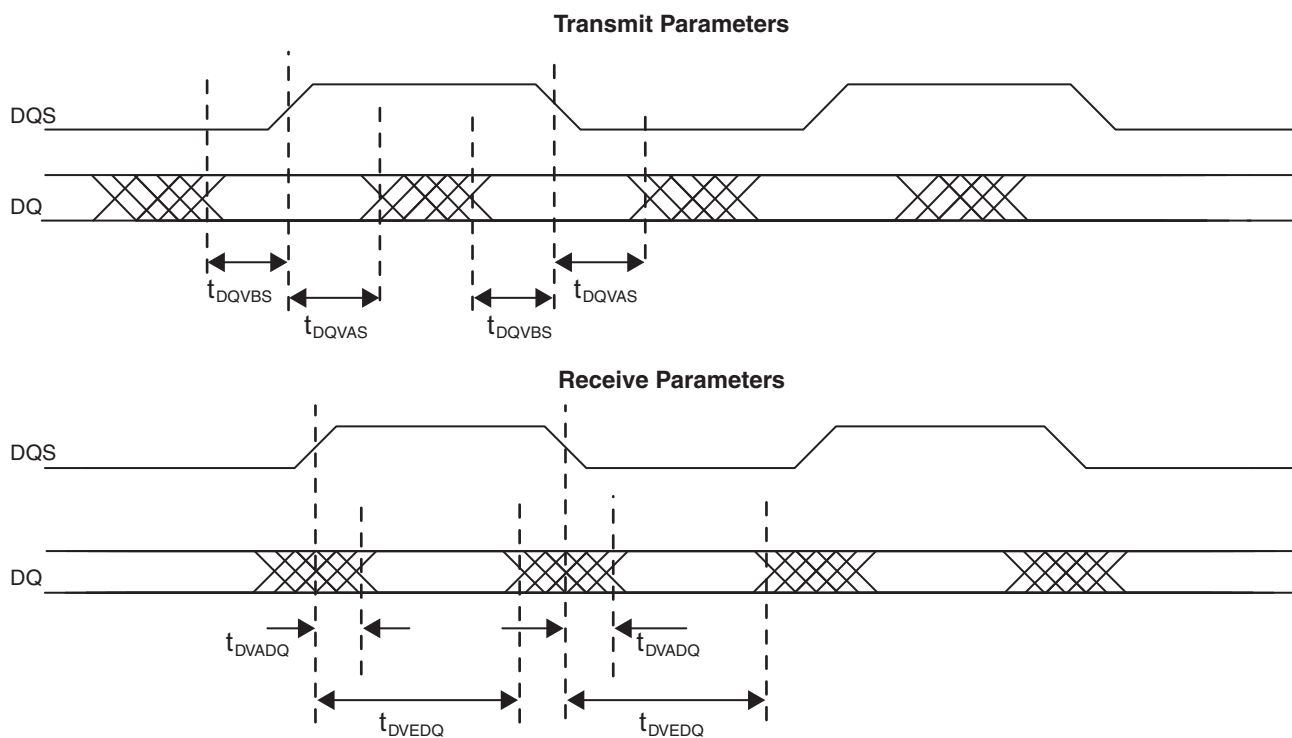


Figure 3-7. DDR/DDR2/DDR3 Parameters



LatticeECP3 Internal Switching Characteristics^{1, 2, 5}

Over Recommended Commercial Operating Conditions

Parameter	Description	-8		-7		-6		Units.
		Min.	Max.	Min.	Max.	Min.	Max.	
PFU/PFF Logic Mode Timing								
tLUT4_PFU	LUT4 delay (A to D inputs to F output)	—	0.147	—	0.163	—	0.179	ns
tLUT6_PFU	LUT6 delay (A to D inputs to OFX output)	—	0.281	—	0.335	—	0.379	ns
tLSR_PFU	Set/Reset to output of PFU (Asynchronous)	—	0.593	—	0.674	—	0.756	ns
tLSRREC_PFU	Asynchronous Set/Reset recovery time for PFU Logic		0.298		0.345		0.391	ns
tSUM_PFU	Clock to Mux (M0,M1) Input Setup Time	0.134	—	0.144	—	0.153	—	ns
tHM_PFU	Clock to Mux (M0,M1) Input Hold Time	−0.097	—	−0.103	—	−0.109	—	ns
tSUD_PFU	Clock to D input setup time	0.061	—	0.068	—	0.075	—	ns
tHD_PFU	Clock to D input hold time	0.019	—	0.013	—	0.015	—	ns
tCK2Q_PFU	Clock to Q delay, (D-type Register Configuration)	—	0.243	—	0.273	—	0.303	ns
PFU Dual Port Memory Mode Timing								
tCORAM_PFU	Clock to Output (F Port)	—	0.710	—	0.803	—	0.897	ns
tSUDATA_PFU	Data Setup Time	−0.137	—	−0.155	—	−0.174	—	ns
tHDATA_PFU	Data Hold Time	0.188	—	0.217	—	0.246	—	ns
tSUADDR_PFU	Address Setup Time	−0.227	—	−0.257	—	−0.286	—	ns
tHADDR_PFU	Address Hold Time	0.240	—	0.275	—	0.310	—	ns
tSUWREN_PFU	Write/Read Enable Setup Time	−0.055	—	−0.055	—	−0.063	—	ns
tHWREN_PFU	Write/Read Enable Hold Time	0.059	—	0.059	—	0.071	—	ns
PIC Timing								
PIO Input/Output Buffer Timing								
tIN_PIO	Input Buffer Delay (LVCMOS25)	—	0.423	—	0.466	—	0.508	ns
tOUT_PIO	Output Buffer Delay (LVCMOS25)	—	1.241	—	1.301	—	1.361	ns
IOLOGIC Input/Output Timing								
tSUI_PIO	Input Register Setup Time (Data Before Clock)	0.956	—	1.124	—	1.293	—	ns
tHI_PIO	Input Register Hold Time (Data after Clock)	0.225	—	0.184	—	0.240	—	ns
tCOO_PIO	Output Register Clock to Output Delay ⁴	-	1.09	-	1.16	-	1.23	ns
tSUCE_PIO	Input Register Clock Enable Setup Time	0.220	—	0.185	—	0.150	—	ns
tHCE_PIO	Input Register Clock Enable Hold Time	−0.085	—	−0.072	—	−0.058	—	ns
tSULSR_PIO	Set/Reset Setup Time	0.117	—	0.103	—	0.088	—	ns
tHLSR_PIO	Set/Reset Hold Time	−0.107	—	−0.094	—	−0.081	—	ns
EBR Timing								
tCO_EBR	Clock (Read) to output from Address or Data	—	2.78	—	2.89	—	2.99	ns
tCOO_EBR	Clock (Write) to output from EBR output Register	—	0.31	—	0.32	—	0.33	ns
tSUDATA_EBR	Setup Data to EBR Memory	−0.218	—	−0.227	—	−0.237	—	ns
tHDATA_EBR	Hold Data to EBR Memory	0.249	—	0.257	—	0.265	—	ns
tSUADDR_EBR	Setup Address to EBR Memory	−0.071	—	−0.070	—	−0.068	—	ns
tHADDR_EBR	Hold Address to EBR Memory	0.118	—	0.098	—	0.077	—	ns
tSUWREN_EBR	Setup Write/Read Enable to EBR Memory	−0.107	—	−0.106	—	−0.106	—	ns

LatticeECP3 sysCONFIG Port Timing Specifications

Over Recommended Operating Conditions

Parameter	Description		Min.	Max.	Units
POR, Configuration Initialization, and Wakeup					
t _{ICFG}	Time from the Application of V _{CC} , V _{CCAUX} or V _{CCIO8} * (Whichever is the Last to Cross the POR Trip Point) to the Rising Edge of INITN	Master mode	—	23	ms
		Slave mode	—	6	ms
t _{VMC}	Time from t _{ICFG} to the Valid Master MCLK		—	5	μs
t _{PRGM}	PROGRAMN Low Time to Start Configuration		25	—	ns
t _{PRGMRJ}	PROGRAMN Pin Pulse Rejection		—	10	ns
t _{DPPINIT}	Delay Time from PROGRAMN Low to INITN Low		—	37	ns
t _{DPPDONE}	Delay Time from PROGRAMN Low to DONE Low		—	37	ns
t _{DINIT} ¹	PROGRAMN High to INITN High Delay		—	1	ms
t _{MWC}	Additional Wake Master Clock Signals After DONE Pin is High		100	500	cycles
t _{CZ}	MCLK From Active To Low To High-Z		—	300	ns
t _{IODISS}	User I/O Disable from PROGRAMN Low		—	100	ns
t _{IOENSS}	User I/O Enabled Time from CCLK Edge During Wake-up Sequence		—	100	ns
All Configuration Modes					
t _{SUCDI}	Data Setup Time to CCLK/MCLK		5	—	ns
t _{HCDI}	Data Hold Time to CCLK/MCLK		1	—	ns
t _{CODO}	CCLK/MCLK to DOUT in Flowthrough Mode		-0.2	12	ns
Slave Serial					
t _{SSCH}	CCLK Minimum High Pulse		5	—	ns
t _{SSCL}	CCLK Minimum Low Pulse		5	—	ns
f _{CCLK}	CCLK Frequency	Without encryption	—	33	MHz
		With encryption	—	20	MHz
Master and Slave Parallel					
t _{SUCS}	CSN[1:0] Setup Time to CCLK/MCLK		7	—	ns
t _{HCS}	CSN[1:0] Hold Time to CCLK/MCLK		1	—	ns
t _{SUWD}	WRITEN Setup Time to CCLK/MCLK		7	—	ns
t _{HWD}	WRITEN Hold Time to CCLK/MCLK		1	—	ns
t _{DCB}	CCLK/MCLK to BUSY Delay Time		—	12	ns
t _{CORD}	CCLK to Out for Read Data		—	12	ns
t _{BSCH}	CCLK Minimum High Pulse		6	—	ns
t _{BSCL}	CCLK Minimum Low Pulse		6	—	ns
t _{BSCYC}	Byte Slave Cycle Time		30	—	ns
f _{CCLK}	CCLK/MCLK Frequency	Without encryption	—	33	MHz
		With encryption	—	20	MHz
Master and Slave SPI					
t _{CFGX}	INITN High to MCLK Low		—	80	ns
t _{CSSPI}	INITN High to CSSPIN Low		0.2	2	μs
t _{SOCDO}	MCLK Low to Output Valid		—	15	ns
t _{CSPID}	CSSPIN[0:1] Low to First MCLK Edge Setup Time		0.3		μs
f _{CCLK}	CCLK Frequency	Without encryption	—	33	MHz
		With encryption	—	20	MHz
t _{SSCH}	CCLK Minimum High Pulse		5	—	ns

LatticeECP3 sysCONFIG Port Timing Specifications (Continued)

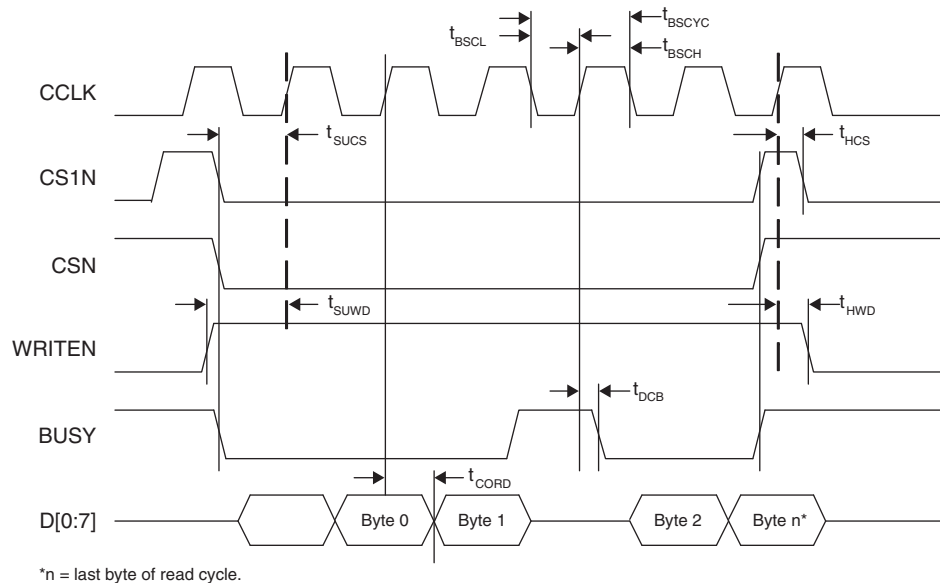
Over Recommended Operating Conditions

Parameter	Description	Min.	Max.	Units
t_{SSCL}	CCLK Minimum Low Pulse	5	—	ns
t_{HLCH}	HOLDN Low Setup Time (Relative to CCLK)	5	—	ns
t_{CHHH}	HOLDN Low Hold Time (Relative to CCLK)	5	—	ns
Master and Slave SPI (Continued)				
t_{CHHL}	HOLDN High Hold Time (Relative to CCLK)	5	—	ns
t_{HHCH}	HOLDN High Setup Time (Relative to CCLK)	5	—	ns
t_{HLQZ}	HOLDN to Output High-Z	—	9	ns
t_{HHQX}	HOLDN to Output Low-Z	—	9	ns

1. Re-toggling the PROGRAMN pin is not permitted until the INITN pin is high. Avoid consecutive toggling of the PROGRAMN.

Parameter	Min.	Max.	Units
Master Clock Frequency	Selected value - 15%	Selected value + 15%	MHz
Duty Cycle	40	60	%

Figure 3-20. sysCONFIG Parallel Port Read Cycle



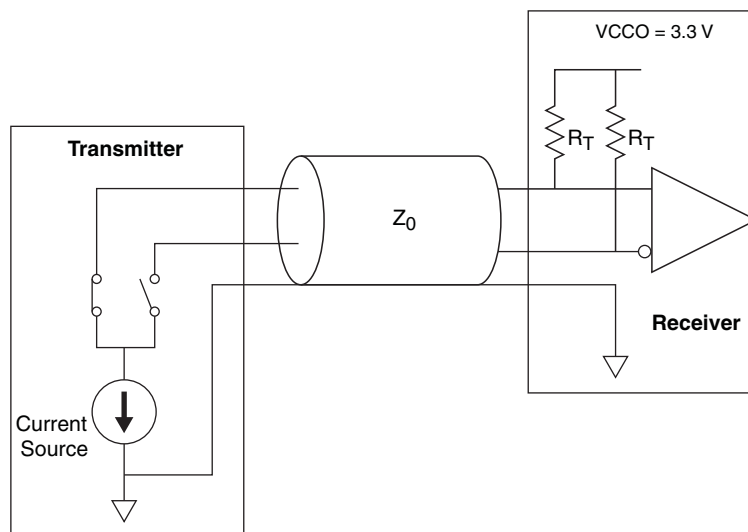
sysI/O Differential Electrical Characteristics

Transition Reduced LVDS (TRLVDS DC Specification)

Over Recommended Operating Conditions

Symbol	Description	Min.	Nom.	Max.	Units
V_{CCO}	Driver supply voltage (+/- 5%)	3.14	3.3	3.47	V
V_{ID}	Input differential voltage	150	—	1200	mV
V_{ICM}	Input common mode voltage	3	—	3.265	V
V_{CCO}	Termination supply voltage	3.14	3.3	3.47	V
R_T	Termination resistance (off-chip)	45	50	55	Ohms

Note: LatticeECP3 only supports the TRLVDS receiver.



Mini LVDS

Over Recommended Operating Conditions

Parameter Symbol	Description	Min.	Typ.	Max.	Units
Z_O	Single-ended PCB trace impedance	30	50	75	Ohms
R_T	Differential termination resistance	50	100	150	Ohms
V_{OD}	Output voltage, differential, $ V_{OP} - V_{OM} $	300	—	600	mV
V_{OS}	Output voltage, common mode, $ V_{OP} + V_{OM} /2$	1	1.2	1.4	V
ΔV_{OD}	Change in V_{OD} , between H and L	—	—	50	mV
ΔV_{ID}	Change in V_{OS} , between H and L	—	—	50	mV
V_{THD}	Input voltage, differential, $ V_{INP} - V_{INM} $	200	—	600	mV
V_{CM}	Input voltage, common mode, $ V_{INP} + V_{INM} /2$	$0.3 + (V_{THD}/2)$	—	$2.1 - (V_{THD}/2)$	
T_R, T_F	Output rise and fall times, 20% to 80%	—	—	550	ps
T_{ODUTY}	Output clock duty cycle	40	—	60	%

Note: Data is for 6 mA differential current drive. Other differential driver current options are available.

PICs and DDR Data (DQ) Pins Associated with the DDR Strobe (DQS) Pin

PICs Associated with DQS Strobe	PIO Within PIC	DDR Strobe (DQS) and Data (DQ) Pins
For Left and Right Edges of the Device		
P[Edge] [n-3]	A	DQ
	B	DQ
P[Edge] [n-2]	A	DQ
	B	DQ
P[Edge] [n-1]	A	DQ
	B	DQ
P[Edge] [n]	A	[Edge]DQSn
	B	DQ
P[Edge] [n+1]	A	DQ
	B	DQ
P[Edge] [n+2]	A	DQ
	B	DQ
For Top Edge of the Device		
P[Edge] [n-3]	A	DQ
	B	DQ
P[Edge] [n-2]	A	DQ
	B	DQ
P[Edge] [n-1]	A	DQ
	B	DQ
P[Edge] [n]	A	[Edge]DQSn
	B	DQ
P[Edge] [n+1]	A	DQ
	B	DQ
P[Edge] [n+2]	A	DQ
	B	DQ

Note: "n" is a row PIC number.

Pin Information Summary (Cont.)

Pin Information Summary		ECP3-95EA			ECP3-150EA	
Pin Type		484 fpBGA	672 fpBGA	1156 fpBGA	672 fpBGA	1156 fpBGA
General Purpose Inputs/Outputs per bank	Bank 0	42	60	86	60	94
	Bank 1	36	48	78	48	86
	Bank 2	24	34	36	34	58
	Bank 3	54	59	86	59	104
	Bank 6	63	67	86	67	104
	Bank 7	36	48	54	48	76
	Bank 8	24	24	24	24	24
General Purpose Inputs per Bank	Bank 0	0	0	0	0	0
	Bank 1	0	0	0	0	0
	Bank 2	4	8	8	8	8
	Bank 3	4	12	12	12	12
	Bank 6	4	12	12	12	12
	Bank 7	4	8	8	8	8
	Bank 8	0	0	0	0	0
General Purpose Outputs per Bank	Bank 0	0	0	0	0	0
	Bank 1	0	0	0	0	0
	Bank 2	0	0	0	0	0
	Bank 3	0	0	0	0	0
	Bank 6	0	0	0	0	0
	Bank 7	0	0	0	0	0
	Bank 8	0	0	0	0	0
Total Single-Ended User I/O		295	380	490	380	586
VCC		16	32	32	32	32
VCCAUX		8	12	16	12	16
VTT		4	4	8	4	8
VCCA		4	8	16	8	16
VCCPLL		4	4	4	4	4
VCCIO	Bank 0	2	4	4	4	4
	Bank 1	2	4	4	4	4
	Bank 2	2	4	4	4	4
	Bank 3	2	4	4	4	4
	Bank 6	2	4	4	4	4
	Bank 7	2	4	4	4	4
	Bank 8	2	2	2	2	2
VCCJ		1	1	1	1	1
TAP		4	4	4	4	4
GND, GNDIO		98	139	233	139	233
NC		0	0	238	0	116
Reserved ¹		2	2	2	2	2
SERDES		26	52	78	52	104
Miscellaneous Pins		8	8	8	8	8
Total Bonded Pins		484	672	1156	672	1156

Package Pinout Information

Package pinout information can be found under “Data Sheets” on the LatticeECP3 product pages on the Lattice website at <http://www.latticesemi.com/Products/FPGAandCPLD/LatticeECP3> and in the Diamond or ispLEVER software tools. To create pinout information from within ispLEVER Design Planner, select **Tools > Spreadsheet View**. Then select **Select File > Export** and choose a type of output file. To create a pin information file from within Diamond select **Tools > Spreadsheet View** or **Tools > Package View**; then, select **File > Export** and choose a type of output file. See Diamond or ispLEVER Help for more information.

Thermal Management

Thermal management is recommended as part of any sound FPGA design methodology. To assess the thermal characteristics of a system, Lattice specifies a maximum allowable junction temperature in all device data sheets. Designers must complete a thermal analysis of their specific design to ensure that the device and package do not exceed the junction temperature limits. Refer to the Thermal Management document to find the device/package specific thermal values.

For Further Information

For further information regarding Thermal Management, refer to the following:

- [Thermal Management](#) document
- TN1181, [Power Consumption and Management for LatticeECP3 Devices](#)
- Power Calculator tool included with the Diamond and ispLEVER design tools, or as a standalone download from www.latticesemi.com/software

Industrial

The following devices may have associated errata. Specific devices with associated errata will be notated with a footnote.

Part Number	Voltage	Grade	Power	Package ¹	Pins	Temp.	LUTs (K)
LFE3-17EA-6FTN256I	1.2 V	–6	STD	Lead-Free ftBGA	256	IND	17
LFE3-17EA-7FTN256I	1.2 V	–7	STD	Lead-Free ftBGA	256	IND	17
LFE3-17EA-8FTN256I	1.2 V	–8	STD	Lead-Free ftBGA	256	IND	17
LFE3-17EA-6LFTN256I	1.2 V	–6	LOW	Lead-Free ftBGA	256	IND	17
LFE3-17EA-7LFTN256I	1.2 V	–7	LOW	Lead-Free ftBGA	256	IND	17
LFE3-17EA-8LFTN256I	1.2 V	–8	LOW	Lead-Free ftBGA	256	IND	17
LFE3-17EA-6MG328I	1.2 V	–6	STD	Lead-Free csBGA	328	IND	17
LFE3-17EA-7MG328I	1.2 V	–7	STD	Lead-Free csBGA	328	IND	17
LFE3-17EA-8MG328I	1.2 V	–8	STD	Lead-Free csBGA	328	IND	17
LFE3-17EA-6LMG328I	1.2 V	–6	LOW	Green csBGA	328	IND	17
LFE3-17EA-7LMG328I	1.2 V	–7	LOW	Green csBGA	328	IND	17
LFE3-17EA-8LMG328I	1.2 V	–8	LOW	Green csBGA	328	IND	17
LFE3-17EA-6FN484I	1.2 V	–6	STD	Lead-Free fpBGA	484	IND	17
LFE3-17EA-7FN484I	1.2 V	–7	STD	Lead-Free fpBGA	484	IND	17
LFE3-17EA-8FN484I	1.2 V	–8	STD	Lead-Free fpBGA	484	IND	17
LFE3-17EA-6LFN484I	1.2 V	–6	LOW	Lead-Free fpBGA	484	IND	17
LFE3-17EA-7LFN484I	1.2 V	–7	LOW	Lead-Free fpBGA	484	IND	17
LFE3-17EA-8LFN484I	1.2 V	–8	LOW	Lead-Free fpBGA	484	IND	17

1. Green = Halogen free and lead free.

Part Number	Voltage	Grade ¹	Power	Package	Pins	Temp.	LUTs (K)
LFE3-35EA-6FTN256I	1.2 V	–6	STD	Lead-Free ftBGA	256	IND	33
LFE3-35EA-7FTN256I	1.2 V	–7	STD	Lead-Free ftBGA	256	IND	33
LFE3-35EA-8FTN256I	1.2 V	–8	STD	Lead-Free ftBGA	256	IND	33
LFE3-35EA-6LFTN256I	1.2 V	–6	LOW	Lead-Free ftBGA	256	IND	33
LFE3-35EA-7LFTN256I	1.2 V	–7	LOW	Lead-Free ftBGA	256	IND	33
LFE3-35EA-8LFTN256I	1.2 V	–8	LOW	Lead-Free ftBGA	256	IND	33
LFE3-35EA-6FN484I	1.2 V	–6	STD	Lead-Free fpBGA	484	IND	33
LFE3-35EA-7FN484I	1.2 V	–7	STD	Lead-Free fpBGA	484	IND	33
LFE3-35EA-8FN484I	1.2 V	–8	STD	Lead-Free fpBGA	484	IND	33
LFE3-35EA-6LFN484I	1.2 V	–6	LOW	Lead-Free fpBGA	484	IND	33
LFE3-35EA-7LFN484I	1.2 V	–7	LOW	Lead-Free fpBGA	484	IND	33
LFE3-35EA-8LFN484I	1.2 V	–8	LOW	Lead-Free fpBGA	484	IND	33
LFE3-35EA-6FN672I	1.2 V	–6	STD	Lead-Free fpBGA	672	IND	33
LFE3-35EA-7FN672I	1.2 V	–7	STD	Lead-Free fpBGA	672	IND	33
LFE3-35EA-8FN672I	1.2 V	–8	STD	Lead-Free fpBGA	672	IND	33
LFE3-35EA-6LFN672I	1.2 V	–6	LOW	Lead-Free fpBGA	672	IND	33
LFE3-35EA-7LFN672I	1.2 V	–7	LOW	Lead-Free fpBGA	672	IND	33
LFE3-35EA-8LFN672I	1.2 V	–8	LOW	Lead-Free fpBGA	672	IND	33

1. For ordering information on -9 speed grade devices, please contact your Lattice Sales Representative.

Date	Version	Section	Change Summary
			LatticeECP3 Maximum I/O Buffer Speed table – Description column, references to VCCIO = 3.0V changed to 3.3V.
			Updated SERDES External Reference Clock Waveforms.
			Transmitter and Receiver Latency Block Diagram – Updated sections of the diagram to match descriptions on the SERDES/PCS Latency Break-down table.
		Pinout Information	“Logic Signal Connections” section heading renamed “Package Pinout Information”. Software menu selections within this section have been updated.
			Signal Descriptions table – Updated description for V _{CCA} signal.
April 2012	02.2EA	Architecture	Updated first paragraph of Output Register Block section.
			Updated the information about sysIO buffer pairs below Figure 2-38.
			Updated the information relating to migration between devices in the Density Shifting section.
		DC and Switching Characteristics	Corrected the Definitions in the sysCLOCK PLL Timing table for t _{RST} .
		Ordering Information	Updated topside marks with new logos in the Ordering Information section.
February 2012	02.1EA	All	Updated document with new corporate logo.
November 2011	02.0EA	Introduction	Added information for LatticeECP3-17EA, 328-ball csBGA package.
		Architecture	Added information for LatticeECP3-17EA, 328-ball csBGA package.
		DC and Switching Characteristics	Updated LatticeECP3 Supply Current table power numbers.
			Typical Building Block Function Performance table, LatticeECP3 External Switching Characteristics table, LatticeECP3 Internal Switching Characteristics table and LatticeECP3 Family Timing Adders: Added speed grade -9 and updated speed grade -8, -7 and -6 timing numbers.
		Pinout Information	Added information for LatticeECP3-17EA, 328-ball csBGA package.
		Ordering Information	Added information for LatticeECP3-17EA, 328-ball csBGA package.
			Added ordering information for low power devices and -9 speed grade devices.
July 2011	01.9EA	DC and Switching Characteristics	Removed ESD Performance table and added reference to LatticeECP3 Product Family Qualification Summary document.
			sysCLOCK PLL Timing table, added footnote 4.
			External Reference Clock Specification table – removed reference to VREF-CM-AC and removed footnote for VREF-CM-AC.
		Pinout Information	Pin Information Summary table: Corrected VCCIO Bank8 data for LatticeECP3-17EA 256-ball ftBGA package and LatticeECP-35EA 256-ball ftBGA package.
April 2011	01.8EA	Architecture	Updated Secondary Clock/Control Sources text section.
		DC and Switching Characteristics	Added data for 150 Mbps to SERDES Power Supply Requirements table.
			Updated Frequencies in Table 3-6 Serial Output Timing and Levels
			Added Data for 150 Mbps to Table 3-7 Channel Output Jitter
			Corrected External Switching Characteristics table, Description for DDR3 Clock Timing, t _{JIT} .
			Corrected Internal Switching Characteristics table, Description for EBR Timing, t _{SUWREN_EBR} and t _{HWREN_EBR} .
			Added footnote 1 to sysConfig Port Timing Specifications table.
			Updated description for RX-CIDs to 150M in Table 3-9 Serial Input Data Specifications

Date	Version	Section	Change Summary
February 2009	01.0		Updated Simplified Channel Block Diagram for SERDES/PCS Block diagram.
			Updated Device Configuration text section.
			Corrected software default value of MCCLK to be 2.5 MHz.
		DC and Switching Characteristics	Updated VCCOB Min/Max data in Recommended Operating Conditions table.
			Corrected footnote 2 in sysIO Recommended Operating Conditions table.
			Added added footnote 7 for $t_{\text{SKEW_PRIB}}$ to External Switching Characteristics table.
			Added 2-to-1 Gearing text section and table.
			Updated External Reference Clock Specification (refclkp/refclkn) table.
			LatticeECP3 sysCONFIG Port Timing Specifications - updated t_{DINIT} information.
			Added sysCONFIG Port Timing waveform.
			Serial Input Data Specifications table, delete Typ data for $V_{\text{RX-DIFF-S}}$.
			Added footnote 4 to sysCLOCK PLL Timing table for t_{PFD} .
			Added SERDES/PCS Block Latency Breakdown table.
			External Reference Clock Specifications table, added footnote 4, add symbol name vREF-IN-DIFF.
			Added SERDES External Reference Clock Waveforms.
			Updated Serial Output Timing and Levels table.
			Pin-to-pin performance table, changed "typically 3% slower" to "typically slower".
			Updated timing information
			Updated SERDES minimum frequency.
			Added data to the following tables: External Switching Characteristics, Internal Switching Characteristics, Family Timing Adders, Maximum I/O Buffer Speed, DLL Timing, High Speed Data Transmitter, Channel Output Jitter, Typical Building Block Function Performance, Register-to-Register Performance, and Power Supply Requirements.
			Updated Serial Input Data Specifications table.
			Updated Transmit table, Serial Rapid I/O Type 2 Electrical and Timing Characteristics section.
		Pinout Information	Updated Signal Description tables.
			Updated Pin Information Summary tables and added footnote 1.
February 2009	01.0	—	Initial release.